

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











30V N-Channel Power MOSFET

TO-252 (DPAK)

2 65 2 3

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

Key Parameter Performance

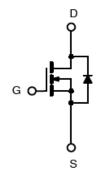
Parameter		Value	Unit	
$V_{ t DS}$		30	V	
R _{DS(on)} (max)	$V_{GS} = 10V$	6	mΩ	
	$V_{GS} = 4.5V$	9		
Q_{g}		11.1	nC	

Ordering Information

Part No.	Package Packing	
TSM060N03CP ROG	TO-252	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Duois Current	T _C =25ºC		80	Α
Continuous Drain Current	T _C =100 ^o C	I _D	51	Α
Pulsed Drain Current (Note 1)		I _{DM}	320	Α
Single Pulse Avalanche Energy (Note 2)		E _{AS}	88	mJ
Single Pulse Avalanche Current (Note 2)		I _{AS}	42	Α
Total Power Dissipation	@ T _C =25°C	Б	54	W
	Derate above T _C =25°C	- P _D	0.43	W/ºC
Operating Junction Temperature		TJ	150	∘C
Storage Temperature Range		T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R _{eJC}	2.3	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W



30V N-Channel Power MOSFET



Electrical Specifications (T_C=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 20A$	R _{DS(ON)}		4.8	6	mΩ
	$V_{GS} = 4.5V, I_D = 10A$			6.5	9	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1	1.6	2.5	V
Zone Onto Welliams Busin Organia	$V_{DS} = 30V, V_{GS} = 0V$				1	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 24V, T _J = 125 ^o C	I _{DSS}			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance	$V_{DS} = 10V, I_{D} = 10A$	g _{fs}		18		S
Dynamic						
Total Gate Charge ^(Note 3,4)	$V_{DS} = 15V, I_{D} = 20A,$	Q_g		11.1		nC
Gate-Source Charge ^(Note 3,4)		Q_{gs}		1.85		
Gate-Drain Charge ^(Note 3,4)	$V_{GS} = 4.5V$	Q_{gd}		6.8		
Input Capacitance		C _{iss}		1160		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz	C _{oss}		200		pF
Reverse Transfer Capacitance	7 I = IMIM2	C _{rss}		180		
Gate Resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz	R_g		2.5		Ω
Switching						
Turn-On Delay Time ^(Note 3,4)		t _{d(on)}		7.5		
Turn-On Rise Time ^(Note 3,4)	V _{DD} =15V , V _{GS} =10V ,	t _r		14.5		
Turn-Off Delay Time ^(Note 3,4)	$R_G=3.3\Omega$, $I_D=-15A$	t _{d(off)}		35.2		ns
Turn-Off Fall Time ^(Note 3,4)		t _f		9.6		1
Source-Drain Diode Ratings and C	Characteristic					•
Continuous Drain-Source Diode		I _S			80	Α
Pulse Drain-Source Diode	V _G =V _D =0V , Force Current	I _{SM}			320	Α
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V _{SD}			1	V

Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. V_{DD} =25V, V_{GS} =10V, L=0.1mH, I_{AS} =42A, R_{G} =25 Ω , Starting T_{J} =25 $^{\circ}$ C
- 3. The data tested by pulsed , pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$
- 4. Essentially independent of operating temperature.

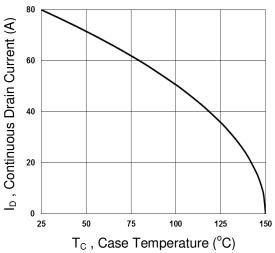


30V N-Channel Power MOSFET

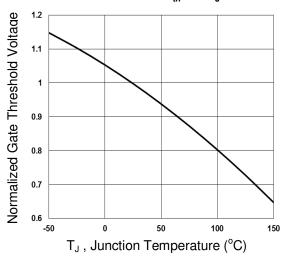
Pb ROHS COMPLIANT

Electrical Characteristics Curve

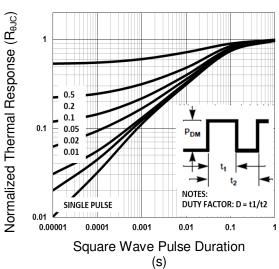
Continuous Drain Current vs. Tc



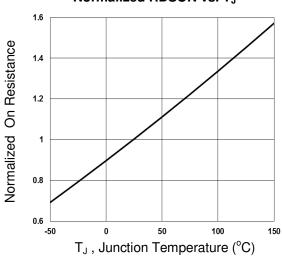
Normalized V_{th} vs. T_J



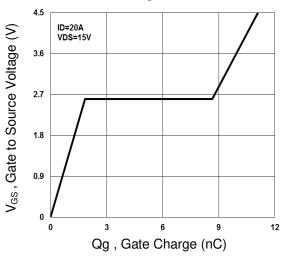
Normalized Transient Impedance



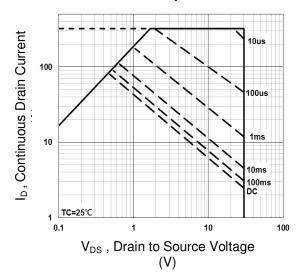
Normalized RDSON vs. T_J



Gate Charge Waveform



Maximum Safe Operation Area

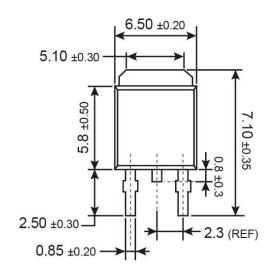


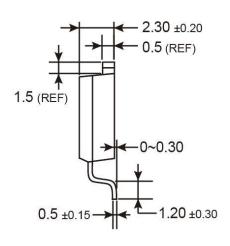


30V N-Channel Power MOSFET



TO-252 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

4/5

L = Lot Code

Version: A14



TSM060N03CP 30V N-Channel Power MOSFET

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.